

# MOSFET – Power, Single N-Channel Logic Level, DPAK

60 V, 54 A, 17 mΩ

NVD5484NL

## Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- High Current Capability
- Avalanche Energy Specified
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain-to-Source Voltage	60	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current $R_{\theta JC}$ (Notes 1 & 3)	$T_C = 25^\circ\text{C}$ 54 $T_C = 100^\circ\text{C}$ 38	A
$P_D$	Power Dissipation $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$ 100 $T_C = 100^\circ\text{C}$ 50	W
$I_D$	Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2 & 3)	$T_A = 25^\circ\text{C}$ 10.7 $T_A = 100^\circ\text{C}$ 7.6	A
$P_D$	Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	$T_A = 25^\circ\text{C}$ 3.9 $T_A = 100^\circ\text{C}$ 2.0	W
$I_{DM}$	Pulsed Drain Current	$T_A = 25^\circ\text{C}$ , $t_p = 10 \mu\text{s}$ 305	A
$I_{Dmaxpk}$	Current Limited by Package (Note 3)	$T_A = 25^\circ\text{C}$ 60	A
$T_J, T_{stg}$	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$
$I_S$	Source Current (Body Diode)	83	A
$E_{AS}$	Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^\circ\text{C}$ , $V_{DD} = 50 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_{L(pk)} = 50 \text{ A}$ , $L = 0.1 \text{ mH}$ , $R_G = 25 \Omega$ )	125	mJ
$T_L$	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	260	$^\circ\text{C}$

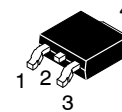
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL RESISTANCE MAXIMUM RATINGS

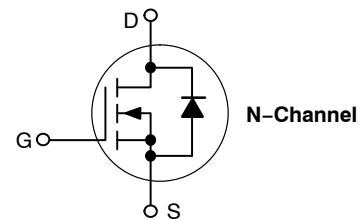
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction-to-Case – Steady State (Drain)	1.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 2)	38	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

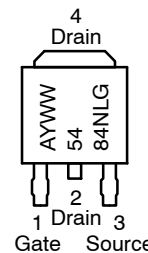
$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$
60 V	17 mΩ @ 10 V 23 mΩ @ 4.5 V	54 A



DPAK  
CASE 369AA  
STYLE 2



## MARKING DIAGRAMS & PIN ASSIGNMENT



- A = Assembly Location\*
- Y = Year
- WW = Work Week
- 5484NL = Device Code
- G = Pb-Free Package

\* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejector pin), the front side assembly code may be blank.

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 5.

# NVD5484NL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60	–	–	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 60 V	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	– –	1.0 10	μA
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V	–		±100	nA

### ON CHARACTERISTICS (Note 4)

V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	1.5	1.9	2.5	V
R <sub>DS(on)</sub>	Drain-to-Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 25 A V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 25 A	– –	13.5 18	17 23	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	–	41	–	S

### CHARGES AND CAPACITANCES

C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = 25 V	–	1410	–	pF
C <sub>oss</sub>	Output Capacitance		–	315	–	
C <sub>rss</sub>	Reverse Transfer Capacitance		–	135	–	
Q <sub>G(TOT)</sub>	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 23 A	V <sub>GS</sub> = 4.5 V V <sub>GS</sub> = 10 V	– –	27 48	nC
Q <sub>G(TH)</sub>	Threshold Gate Charge	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V, I <sub>D</sub> = 23 A	–	0.9	–	
Q <sub>GS</sub>	Gate-to-Source Charge		–	4.4	–	
Q <sub>GD</sub>	Gate-to-Drain Charge		–	19	–	
R <sub>G</sub>	Gate Resistance		–	8.5		Ω

### SWITCHING CHARACTERISTICS (Note 5)

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 48 V, I <sub>D</sub> = 23 A, R <sub>G</sub> = 10 Ω	–	18	–	ns
t <sub>r</sub>	Rise Time		–	160	–	
t <sub>d(off)</sub>	Turn-Off Delay Time		–	100	–	
t <sub>f</sub>	Fall Time		–	110	–	
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V, I <sub>D</sub> = 23 A, R <sub>G</sub> = 10 Ω	–	7.8	–	
t <sub>r</sub>	Rise Time		–	45	–	
t <sub>d(off)</sub>	Turn-Off Delay Time		–	152	–	
t <sub>f</sub>	Fall Time		–	113	–	

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Forward Diode Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 25 A	T <sub>J</sub> = 25°C	–	0.9	1.2	V
			T <sub>J</sub> = 125°C	–	0.8	–	
t <sub>RR</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 23 A		–	64	–	ns
t <sub>a</sub>	Charge Time			–	33	–	
t <sub>b</sub>	Discharge Time			–	31	–	
Q <sub>RR</sub>	Reverse Recovery Charge			–	118	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

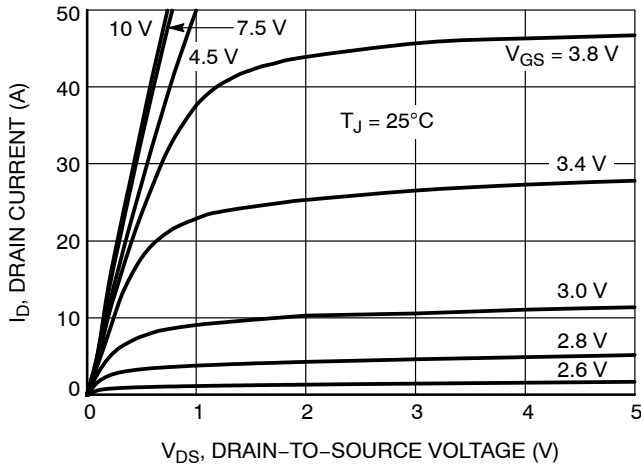


Figure 1. On-Region Characteristics

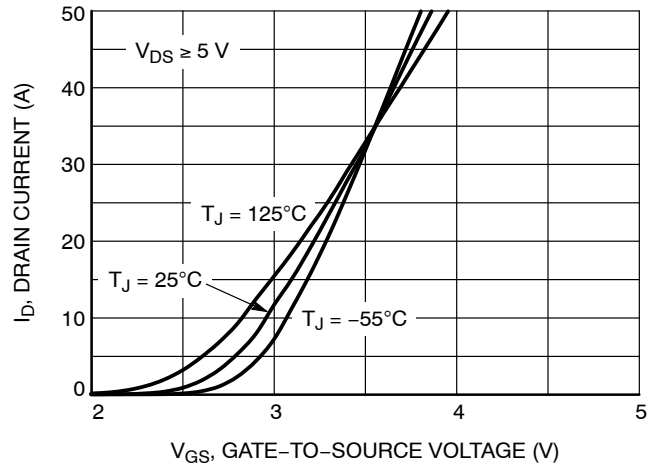


Figure 2. Transfer Characteristics

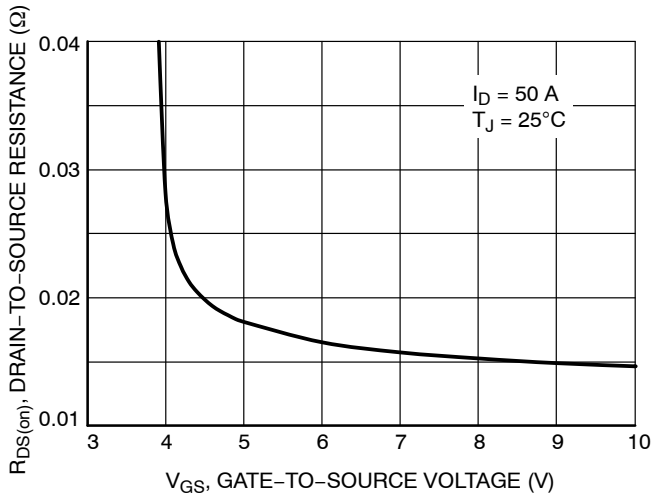


Figure 3. On-Resistance vs. Gate-to-Source Voltage

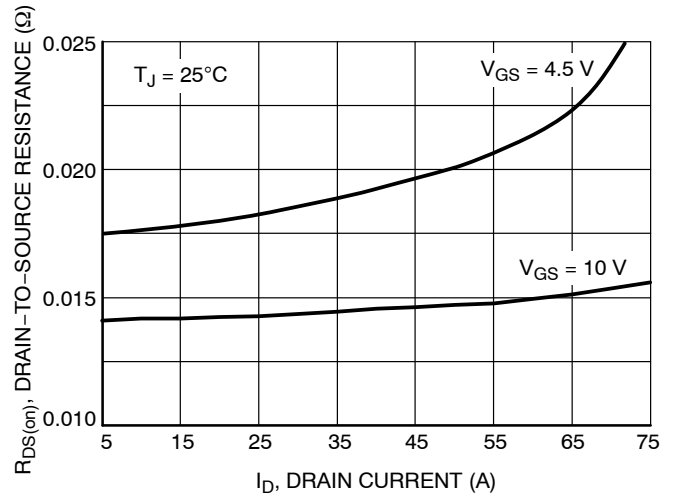


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

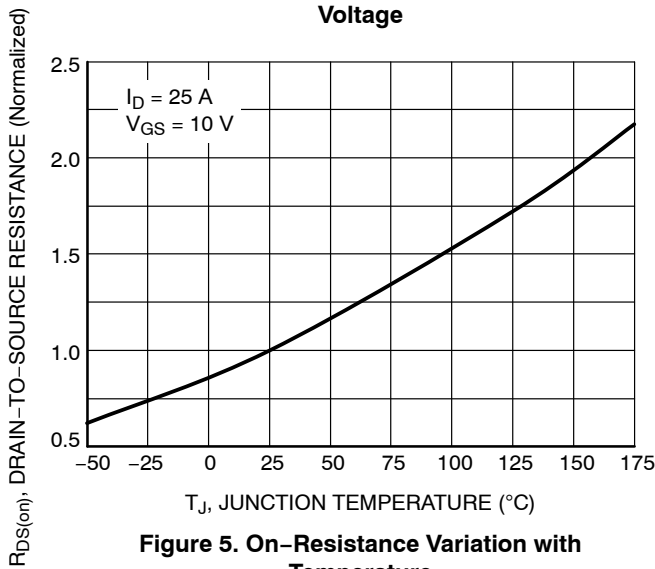


Figure 5. On-Resistance Variation with Temperature

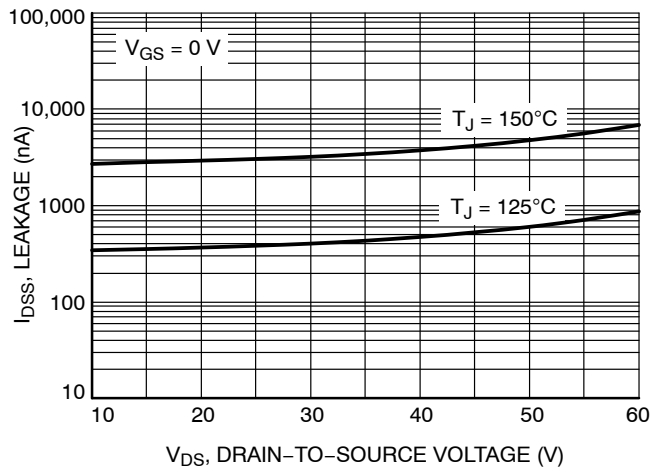


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

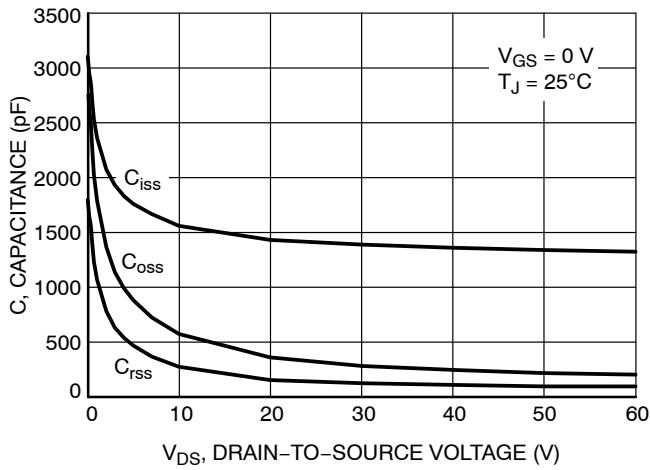


Figure 7. Capacitance Variation

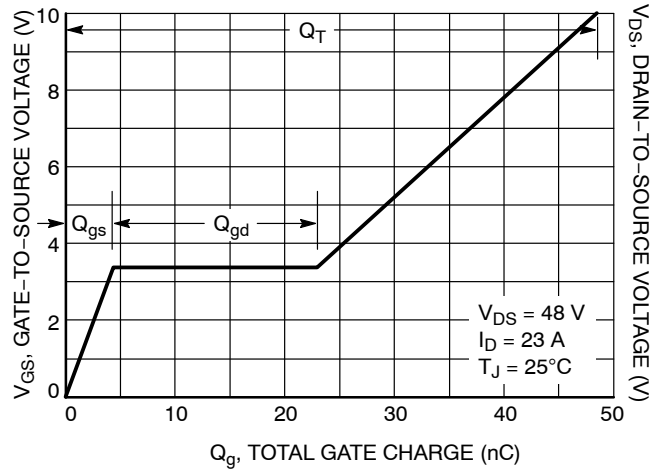


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

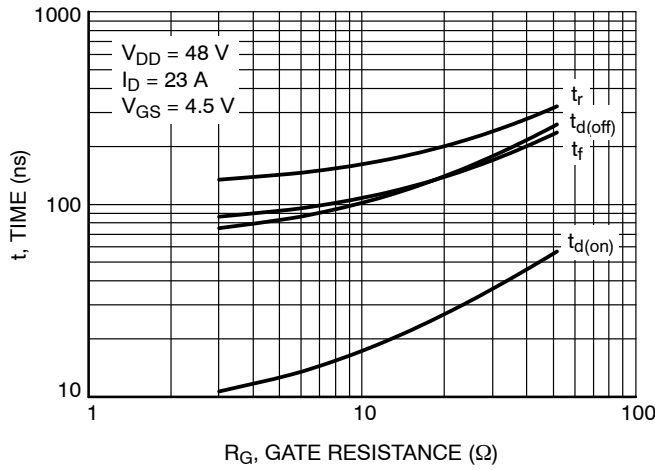


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

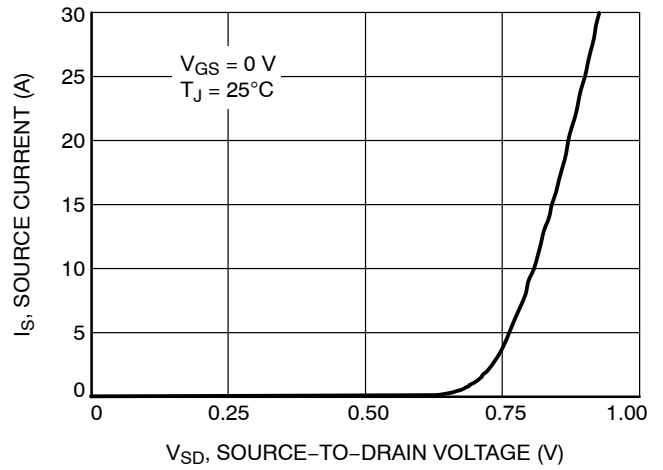


Figure 10. Diode Forward Voltage vs. Current

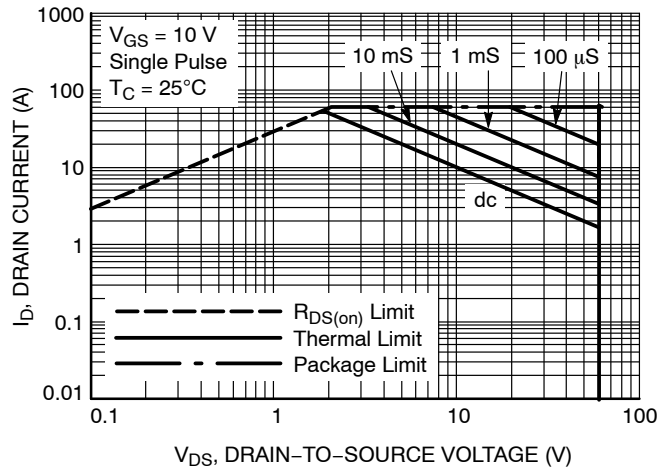


Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NVD5484NL

## TYPICAL CHARACTERISTICS (continued)

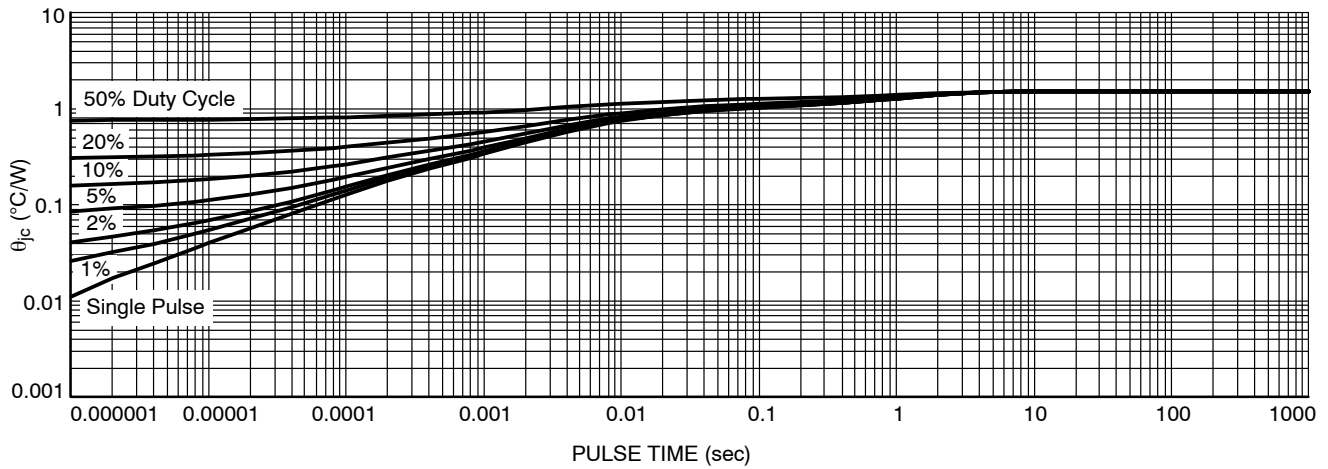


Figure 12. Thermal Response

### ORDERING INFORMATION

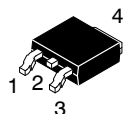
Order Number	Package	Shipping <sup>†</sup>
NVD5484NLT4G-VF01	DPAK (Pb-Free)	2500 / Tape & Reel

### DISCONTINUED (Note 6)

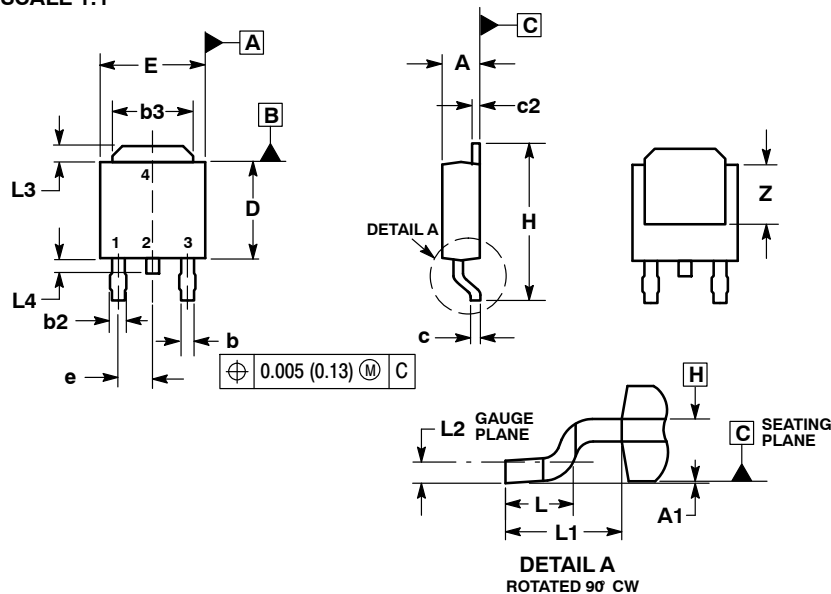
NVD5484NLT4G	DPAK (Pb-Free)	2500 / Tape & Reel
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<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

6. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on [www.onsemi.com](http://www.onsemi.com).



SCALE 1:1



STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 3:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

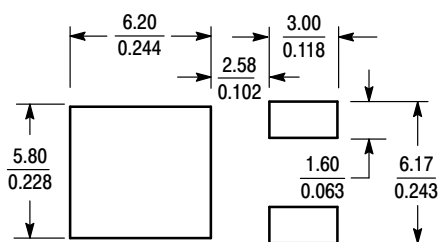
STYLE 4:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 5:  
PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 6:  
PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2

STYLE 7:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

#### SOLDERING FOOTPRINT\*



SCALE 3:1 (mm/inches)

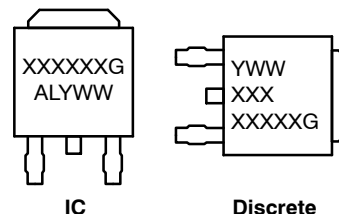
\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

#### GENERIC MARKING DIAGRAM\*



XXXXXX = Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.

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